arXiv:cond-mat/0310612v1 [cond-mat.str-el] 26 Oct 2003

Examining the metal-to-insulator transitions in $Li_{1+x}Ti_{2-x}O_4$ and $LiAl_yTi_{2-y}O_4$ with a Quantum Site Percolation model

F. Fazileh and R. J. Gooding
Department of Physics, Queen's University, Kingston ON K7L 3N6 CANADA

D. C. Johnston
Ames Laboratory and Department of Physics and Astronomy, Iowa State University, Ames, Iowa 50011 USA

(Dated: March 22, 2024)

We have studied the composition-induced metal-to-insulator transitions (MIT) of cation substituted Lithium Titanate, in the forms $Li_{1+x}Ti_{2-x}O_4$ and $LiAl_yTi_{2-y}O_4$, utilising a quantum site percolation model, and we argue that such a model provides a very reliable representation of the non-interacting electrons in this material if strong correlations are ignored. We then determine whether or not such a model of $3d^1$ electrons moving on the Ti (corner-sharing tetrahedral) sublattice describes the observed MITs, with the critical concentration defined by the matching of the mobility edge and the chemical potential. Our analysis leads to quantitative predictions that are in disagreement with those measured experimentally. For example, experimentally for the $LiAl_yTi_{2-y}O_4$ compound an Al concentration of $y_c \simeq 0.33$ produces a metal-to-insulator transition, whereas our analysis of a quantum site percolation model predicts $y_c \simeq 0.83$. One hypothesis that is consistent with these results is that since strong correlations are ignored in our quantum site percolation model, which includes the effects of configurational disorder only, such strong electronic correlations are both present and important.

The oxide spinel $LiTi_2O_4$ has been the subject of considerable experimental and theoretical study. It was first synthesised and structurally characterised in 1971 by Deschanvres et al.[1] Superconductivity, at 11K, was identified in 1973 by one of the present authors and his collaborators.[2] A comprehensive study of the normal state and superconducting properties of $Li_{1+x}Ti_{2-x}O_4$ (for $0 \leq x \leq 1/3$) was reported in 1976,[3,4] and a superconducting transition temperature of 13K was observed. A recent review[5] highlights many of the advances made since then.

There are several reasons to study this system. Firstly, it is interesting to note that superconductivity among spinel systems is very rare; *e.g.*, of the 300 or so known spinels,[5] only four of them are superconductors – $CuRh_2Se_4$ ($T_c = 3.49$ K), CuV_2S_4 ($T_c = 4.45$ K), $CuRh_2S_4$ ($T_c = 4.8$ K), and $LiTi_2O_4$ ($T_c = 11.3$ K) – and only one of these four is an oxide. So, that oxide, $LiTi_2O_4$, has the highest transition temperature of any spinel. Secondly, conduction in this system is believed to take place on the Ti sublattice via the t_{2g} orbitals, as suggested, *e.g.*, by electronic structure calculations,[6,7] and these sites form a corner-sharing tetrahedral lattice (CSTL). Thus, this system represents an example of conduction on a fully frustrated three-dimensional lattice. Also, in this paper we will argue, supported by considerable experimental evidence, that the conduction paths of $Li_{1+x}Ti_{2-x}O_4$ and $LiAl_yTi_{2-y}O_4$ are excellent physical realizations of quantum site percolation.[8,9]

Furthermore, and central to the motivation for our work, these same electronic structure calculations[6,7] point out that this is a narrow band electronic system, with the bandwidth of the t_{2g} bands of the order of 2-3 eV, thus suggesting that perhaps strong electronic correlations are present and important. Indeed, others have reached similar conclusions; notably, the phase diagram of Alex Muller,[10] summarising a view of how the increased strength of electronic correlations in transition metal oxides leads to higher and higher superconducting temperatures, includes the Lithium Titanate system. Although the original experiments and analysis suggested a weak-coupling BCS-like s-wave superconductor,[4] it was later suggested[11] that off stoichiometry this material is in fact an "anomalous" superconductor (although this claim is not without criticism[12]). We also mention that photoemission studies of Edwards, et al.[13] are interpreted in terms of strong correlations, and magnetic susceptibility[14] and specific heat data[11] are interpreted in terms of a density of states that is moderately to strongly enhanced (see Ref.[15] for a discussion of these and other experiments). Taken together, these experimental results form a reasonably strong case for the presence of electronic correlations that are important to the physics of these materials.

Lastly, we mention the recent discovery of the first d-electron heavy fermion compound, LiV_2O_4.[16] This system also assumes the spinel structure, but so far no superconductivity has been observed. The active transition metal ion in LiV_2O_4 has a formal valence of $d^{1.5}$, whereas for $LiTi_2O_4$ one considers $d^{0.5}$ ions. Thus, $LiTi_2O_4$ is a lower electronic density system than LiV_2O_4, and an understanding of its behaviour would seem to be a prerequisite to a full understanding of the Vanadate material. For example, why does $LiTi_2O_4$ superconduct, with a relatively high T_c, while LiV_2O_4 does not superconduct at all?

In attempt to gain more understanding of the $LiTi_2O_4$ system, and, in particular, to try and un-

derstand whether or not strong electronic correlations are present, we have examined the density driven metal-to-insulator transition (MIT) of the related $Li_{1+x}Ti_{2-x}O_4$ and $LiAl_yTi_{2-y}O_4$ compounds; for $x_{MIT} \approx 0.12$ and $y_{MIT} \approx 1/3$, transitions[3,11,17,18,19] to a non-metallic state (which we refer to as insulating) are encountered. To be specific, we use a one electron approach to study this transition employing a quantum site percolation model. Our work may be viewed as addressing the question of whether or not the MIT undergone by this system is driven by disorder only, similar to an Anderson-like MIT. We find that the answer is no, and thus this work provides indirect theoretical support for the proposal that strong electronic correlations are important in a description of the complicated transitions undergone in the $LiTi_2O_4$ class of materials.

To fully explain our model we note the following: (i) Electronic structure calculations[6,7] show that the bands arising from the Ti 3d orbitals are separated from the O 2p band by about 2.4 eV; thus, the electronic valence state may be represented as $Li^{+1}(Ti^{+3.5})_2(O^{-2})_4$, and we ignore the oxygen sites and focus on only the Ti sites. The crystal octahedral field around Ti cations splits the Ti 3d bands into two separate and nonoverlapping t_{2g} and e_g bands, with the e_g bands split off above the t_{2g} bands. Thus, formally this is a very low filling system | 1/12th filling of each of the (approximately) degenerate t_{2g} bands. Although we have generalized our work to include all three t_{2g} bands, here we will present results for a one-band model of the Ti sublattice, and thus the stoichiometric compound is represented by a 1/4-filled band. (ii) Crystallographic refinements of the excess Li system $Li_{1+x}Ti_{2-x}O_4$ and the doped Al system $LiAl_yTi_{2-y}O_4$ have consistently demonstrated that both the excess Li and doped Al ions enters substitutionally onto the Ti sublattice (octahedral sites of the spinel structure).[1,3,19,20,21] Assuming that the Li/Al ions that are substituted into the corner-sharing tetrahedral lattice are fully ionised, these sites would block any conduction electrons from hopping onto such sites; e.g., a simple argument supporting this follows from noting that the Li^+ ions will be at least doubly negatively charged relative to the occupied Ti^{3+} and unoccupied Ti^{4+} sites that would exist in the absence of substituting Li, and thus electrons will avoid these sites in favour of the Ti sites. We shall assume that these Li-substituting sites are removed from the sites available to the conduction electrons, which implies that this system represents an excellent physical realization of site percolation.

Using such a model the simplest approach to characterising the MIT would be to then associate the transition with the critical concentration at which the classical percolation threshold is reached. For corner-sharing tetrahedral lattices, we have completed a large scale Hoshen-Kopelman[22] search, and have determined that this concentration corresponds to a probability of finding an occupied site at the transition of $p_c = 0.39 \pm 0.01$. Noting that the relationship between the probability p of site being occupied by a Ti ion (in the stoichiometric Ti sublattice), and the excess Li concentration x, is given by $x = 2(1-p)$, with an identical $y = 2(1-p)$ relation for Al added to the Ti sublattice, in contrast to previous statements[17,18] this p_c corresponds to a critical excess Li, or added Al, of $x_c = y_c = 2(1-p_c) \approx 1.2$; that is $Li_{2.2}Ti_{0.8}O_4$ or $LiAl_{1.2}Ti_{0.8}O_4$. These very high levels of doping are well beyond the observed $x_{MIT} \approx 0.15$ or $y_{MIT} \approx 0.33$ concentrations at which the MITs occur. In fact, such a system would require large positive Ti valencies well beyond anything seen in nature! Thus, the physics of these MITs is more complicated than simply the loss of an infinite maximally connected cluster at p_c.

We now consider a more accurate model for this system, a so-called quantum site percolation model, which includes the dynamics of the electrons hopping on the conducting, disordered sublattice of Ti sites. To be specific, the near-neighbour tight-binding Hamiltonian for $LiTi_2O_4$ is

$$\hat{H} = \sum_i \varepsilon_i c_i^\dagger c_i - t \sum_{<ij>} (c_i^\dagger c_j + h.c.) \qquad (1)$$

where i labels the sites of the (ordered) Ti sublattice, $c_i^\dagger$ (c_i) is the creation (annihilation) operator of an electron at site i, $\sum_{<ij>}$ represents the sum over all nearest neighbour sites of a corner-sharing tetrahedral lattice, and t is the near-neighbour hopping energy. To produce our model of quantum site percolation for the doped systems, the on-site energy ε_j is determined by the probability of occupation, denoted by p, of a site being either a Ti ion, or a Li or Al dopant ion:

$$P(\varepsilon_i) = p\,(\varepsilon_i - \varepsilon_{Ti}) + (1-p)\,(\varepsilon_i - \varepsilon_X) \qquad (2)$$

where ε_{Ti} (ε_X) is the on-site energy when an electron occupies a Ti (X = Li or Al) site. In order to enforce that itinerant electrons move only on Ti sites we set $\varepsilon_{Ti} = 0$ and $\varepsilon_X \to \infty$, and this limit connects this system with a quantum site percolation Hamiltonian.[8,9] Such considerations lead to the introduction of the quantum percolation threshold,[9] usually denoted by p_q. To be specific, p_q is reached when all single-electron energy eigenstates of the above tight-binding Hamiltonian are localized. That means that p_q is always larger than p_c since the presence of extended states necessarily requires an infinite maximally connected cluster. Further, the evaluation of this quantity is warranted since $p_q > p_c$ implies that the theoretical predictions of x_c and y_c given above would be reduced by quantum percolation.

Our evaluation of p_q for the corner-sharing tetrahedral lattice proceeds as follows. We have considered various realizations of site percolated lattices for several system sizes for a range of dopant concentrations; to be specific, we consider lattices of size two, four, six, and eight cubed conventional unit cells (noting that there are 16 Ti sites in the ordered lattice per conventional unit cell), and then for each p we examine 100, 50, 20 and 10 realizations consistent with this p, for two, four, six, and

eight cubed lattices, respectively. For each realization we first apply the Hoshen-Kopelman algorithm to identify the maximally connected cluster. Then, we diagonalize the one-electron Hamiltonian describing the electron dynamics on this cluster. Then, to determine the localized vs. delocalized nature of the single-electron wave functions for the maximally connected cluster, we have used the scaling of the relative localization length as a function of system size, as described by Sigeti et al.[23] This localization length, for a particular eigenstate, is defined by

$$= \sum_{ij} |_i|^2 |_j|^2 d(i;j) \qquad (3)$$

where $|_i|^2$ is the probability amplitude for this eigenstate at site i, and d(i;j) is the Euclidean distance between lattice sites i and j. Then, the relative localization length is just the ratio of this quantity to that for a state having a uniform probability amplitude throughout the entire maximally connected cluster (we denote the latter by $_0$) | this ratio thus provides a useful measure of the effective size, or localization, of a particular eigenstate relative to a Bloch state on the same maximally connected cluster. The utility of this quantity (and we will describe its use for another problem below) is that if the quantity decreases as the system size is increased, that eigenstate corresponds to one that is spatially localized; the opposite behaviour is expected for delocalized states. We have used this quantity as a means of identifying p_q.

As a test of this method, we note that for three-dimensional lattices, reliable estimates exist only for the simple cubic lattice, and these were obtained with a variety of different methods | e.g., see the discussion in Ref.[24] A value of $p_q = 0:44 \quad 0:02$ was identified,[24] and we have found that our method reproduces this number.

Using this method we find a value of p_q for corner-sharing tetrahedral lattices (with near-neighbour hopping only) of $p_q = 0:52 \quad 0:02$, and if we then associate this quantity with the concentration at which the MIT occurs in doped $LiTi_2O_4$, one finds $x_c = y_c = 2(1 \quad p_q) = 0:96$, which correspond to $Li_{1:96}Ti_{1:04}O_4$ and $LiAl_{0:96}Ti_{1:04}O_4$. Again, these concentrations are much higher than the experimentally measured values.

The reason for both of these failures is clear and has been suggested before[17] | as the concentration of doped cations is increased, the density of available 3d electrons is decreased. In fact, for $x_{BI} \quad 0:33$ and $y_{BI} \quad 1:0$ these materials become insulators simply because the bands of all allowed states are empty (we refer to such a state as a Band Insulator (BI)). So, if a one-electron description is going to correctly reproduce the MIT, we must account for the changing of the electronic density with cation dopant concentration. (This notwithstanding, we needed to determine what values of x_c and y_c were predicted by p_q in case they were less than either x_{BI}, or y_{BI}, respectively. Clearly, they are not.)

Also, since the above arguments point to Ti occupation probabilities well above the quantum percolation

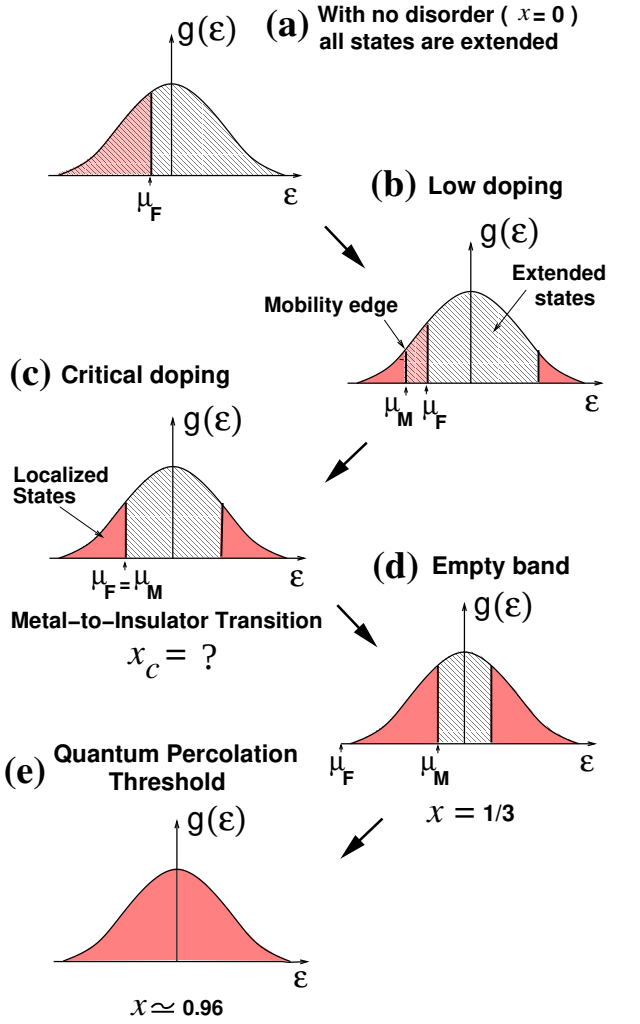

FIG. 1: A sequence of schematic diagrams that summarize how the MIT in $Li_{1+x}Ti_{2-x}O_4$ would proceed if the transition was caused by disorder only. The densities of states vs. energy are shown for several x. The hatched regions identify the location of extended states, and the unhatched (solid) regions of density of states represent the location of localized states. (a) In $LiTi_2O_4$ all eigenstates are extended and the system is a $\frac{1}{4}$-filled d band conductor. (b) By doping Li cations randomly into the Ti sites the system becomes disordered; thus, some energy eigenstates near the band edges become localized, and, in particular, all states below the mobility edge $_M$ are localized. At the same time the density of itinerant electrons decreases, and thus the chemical potential ($_F$) is reduced. (c) When the chemical potential coincides with the mobility-edge, this model would predict that the MIT occurs. (d) The other end member of the homogeneity range of the spinel phase $Li_{1+x}Ti_{2-x}O_4$ ($0 \quad x \quad \frac{1}{3}$) is an empty band insulator (note that the chemical potential appears at the bottom of the allowed energy bands, and thus all electronic states are unoccupied). (e) The so-called quantum percolation threshold is reached when all electronic states have a localized character (regardless of the location of the chemical potential).

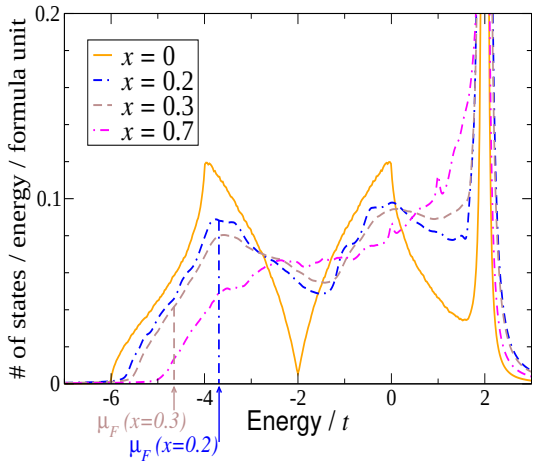

FIG. 2: Averaged numerical density of states for $Li_{1+x}Ti_{2-x}O_4$ systems with different doping concentrations, and the corresponding location of chemical potentials. The DOS of the undoped system corresponds to the thermodynamic limit, whereas plots for the doped systems are averaged density of states for 8^3 conventional unit cells using 10 different realizations of disorder.

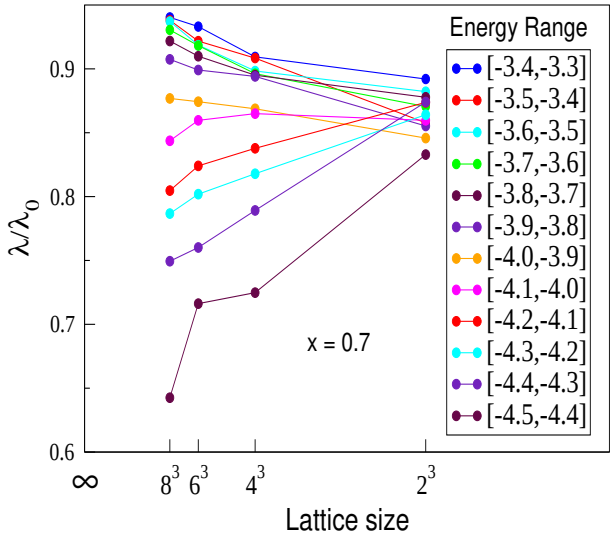

FIG. 3: Scaling of the relative localization length ( ) of different energy "bins" relative to that of the maximally connected cluster ($_0$), for energies close to the mobility edge, for a doping concentration of $x = 0.7$. This ratio is plotted vs. the reciprocal of the number of conventional cells, and as the size of the lattices is increased from 2^3 conventional unit cells to 8^3 unit cells this data shows that the eigenstates with energies above -3.9 have delocalized behaviour. For this system we estimate that the (lower) mobility edge is located at 4:0 0:15.

threshold, one is guaranteed to find a maximally connected cluster, and (possibly) several isolated clusters. By definition, all electronic states associated with an isolated cluster are localized, while for the maximally connected cluster both extended and localized states will be found. Similar to Anderson localization[25] of disordered systems, we expect that the eigenstates of the maximally connected cluster are localized in the band-edge and are separated from extended states at the middle of the band by the so-called mobility-edge.[25] By increasing disorder more and more states become localized and the mobility-edge moves toward the centre of the band. However, as the concentration of cations (producing the disorder) is increased the density of itinerant 3d electrons is decreased. As long as the system's chemical potential (determined by both the density of 3d electrons and electronic density of states of the disordered system) is above the mobility edge, the system remains metallic, whereas if it was below the mobility edge, the states in the immediate vicinity of the Fermi surface would be localized and the system would display insulating behaviour. The critical dopant concentration at which the chemical potential and mobility edge meet thus identifies the MIT. The diagrams in Fig. 1 summarize this process for the particular example of $Li_{1+x}Ti_{2-x}O_4$ (for which x_c 0:15 and x_{BI} 0:33).

Example density of states curves, and the locations of the chemical potentials, are shown in Fig. 2 for different doping concentrations, averaged over systems with 8-cubed conventional unit cells (the largest studied). Note that the full spectrum of eigenvalues, of both the maximally connected cluster and all isolated clusters, have been evaluated since the latter contribute to the location of the chemical potential.

The mobility edge has been estimated using the above-mentioned scaling method,[23] and Fig. 3 depicts the application of this method to identify the location of mobility edge for the specific doping concentration of $x = 0.7$. To be concrete, one can estimate that for this dopant concentration the mobility edge, in units of the hopping energy t, is -4.0 0.15.

We have combined all of our data in Fig. 4, which shows the chemical potential and mobility edge that we would estimate for both the excess Li and doped Al systems. For reference we have included the values of the band minimum for all dopings. Note that the Fermi level of the excess Li system crosses the mobility edge at roughly x_c 0:324, whereas for the doped Al system this crossing occurs at y_c 0:83. Clearly, these numbers are much larger than the experimental values (x_{MIT} 0:15 and y_{MIT} 0:33). Thus, we have studied a system that should be very well represented, in a one-electron theory, by a quantum site percolation model, have determined the concentrations at which the Fermi levels cross the mobility edge, and find these values to be a factors of 2 and greater than 3 larger than the experimental results. So, we believe that this shows that a one-electron model, that ignores electronic correlations, cannot explain the observed MITs.

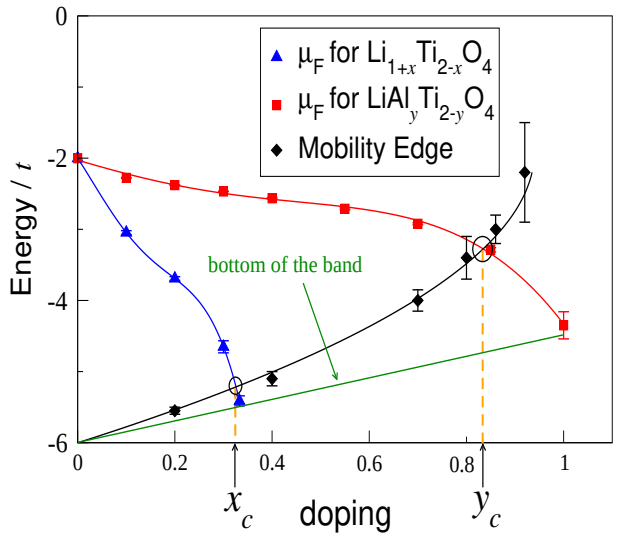

FIG. 4: This plot displays the final numerical results of our study, and leads to the identification of predicted concentrations at which the MITs occur. These data are the the chemical potentials ($_F$) and mobility edge as a function of doping for both $Li_{1+x}Ti_{2-x}O_4$ and $LiAl_yTi_{2-y}O_4$; for reference we have also plotted the minimum of the band of electronic states. The crossing of the chemical potential and mobility edge (denoted by open black circles) would indicate the position of disorder-only induced metal-to-insulator transition, and these values are labelled x_c and y_c.

Concluding, our results show that disorder-only models of the MITs undergone by these systems substantially overestimate the critical concentrations of doped cations. To be specific, for $Li_{1+x}Ti_{2-x}O_4$ our numerical result for x_c is a little more than double the experimental value, and for $LiAl_yTi_{2-y}O_4$ our numerical result is an even larger multiple. (We note that we have not eliminated the possibility that polaronic effects give rise to this transition, although no experimental work points to their existence.[5]) Thus, indirectly, this study supports the hypothesis that strong electronic correlations are important for the MIT, and, possibly, also for the T_c 13K superconducting transition undergone by $LiTi_2O_4$.

This past year[26] sample preparation advances have allowed for the growth of large stoichiometric $LiTi_2O_4$ single crystals, and a remarkably sharp superconducting transition (T_c 0.1 K) has been observed. We hope that these new samples stimulate further experimental research in this interesting class of materials.

We wish to thank Gene Golub for several helpful comments. Part of this paper was written when one of the authors (RJG) was visiting the Fields Institute for Research in Mathematical Sciences, and he thanks them for their support and hospitality. This work was supported in part by the NSERC of Canada, OGSST, and the US-DOE.

[1] A. Deschanvres, B. Raveau, and Z. Sekkal, Mater. Res. Bull. 6, 699 (1971).
[2] D. C. Johnston, H. Prakash, W. H. Zachariasen, and R. Viswanathan, Mater. Res. Bull. 8, 777 (1973).
[3] D. C. Johnston, J. Low Temp. Phys. 25, 145 (1976).
[4] R. W. McCallum, D. C. Johnston, C. A. Luengo, and M. B. Maple, J. Low Temp. Phys. 25, 177 (1976).
[5] E. G. Moshopoulou, J. Am. Ceram. Soc. 82, 3317 (1999).
[6] S. Satpathy and R. M. Martin, Phys. Rev. B 36, 7269 (1987).
[7] S. Massidda, J. Yu, and A. J. Freeman, Phys. Rev. B 38, 11352 (1988).
[8] S. Kirkpatrick and T. P. Eggarter, Phys. Rev. B 6, 3598 (1972).
[9] Y. Shapir, A. Aharony, and A. B. Harris, Phys. Rev. Lett. 49, 486 (1982).
[10] K. A. Muller, in Proceedings of the 10th Anniversary HTS Workshop on Physics, Materials, and Applications, edited by B. Batlogg et al. (World Scientific, 1996), p. 1.
[11] J. M. Heintz et al., Cond. Mat.: Z. Phys. B 76, 303 (1989).
[12] J. F. Annett, Physica C 318, 1 (1999).
[13] P. P. Edwards et al., J. Sol. St. Chem. 54, 127 (1984).
[14] M. R. Harrison, P. P. Edwards, and J. B. Goodenough, J. Sol. St. Chem. 54, 136 (1984).
[15] D. P. Dunstall et al., Phys. Rev. B 50, 16451 (1994).
[16] S. Kondo, D. C. Johnston, et al., Phys. Rev. Lett. 78, 3729 (1997).
[17] M. R. Harrison, P. P. Edwards, and J. B. Goodenough, Phil. Mag. B 52, 679 (1985).
[18] P. M. Lambert et al., in Disordered Semiconductors, edited by M. A. Kastner et al. (Plenum Press, 1987), pp. 135{149.
[19] P. M. Lambert, P. P. Edwards, and M. R. Harrison, J. Sol. St. Chem. 89, 345 (1990).
[20] M. R. Harrison, PhD. thesis, Oxford University (1981).
[21] P. M. Lambert, PhD. thesis, Cornell University (1986).
[22] J. Hoshen and R. Kopelman, Phys. Rev. B 14, 3438 (1976).
[23] D. E. Sigeti et al., Phys. Rev. B 44, 614 (1991).
[24] C. M. Soukoulis, Q. Li, and G. S. Grest, Phys. Rev. B 45, 7724 (1992).
[25] P. W. Anderson, Phys. Rev. 109, 1492 (1958).
[26] C. Chen et al., J. Crystal Growth 250, 139 (2003).